ECOLE POLYTECHNIQUE FEDERALE DE LAUSANNE (EPFL)
CENTER OF MICRO-NANO-TECHNOLOGY (CMI)

SOI WAFERS - SPECIFICATION SOI-380-2-100

Rev. 1.1 / 25.04.06

Overall wafer

Growth method:	CZ
Bonding method:	Fusion bonding
Diameter:	100 ± 0.5mm
Primary Flat Orientation:	{110} ± 0.5°
Primary Flat Length:	32.5 ± 2.5 mm
Non-SOI edge area:	< 1.5mm (preferably 0mm if not affecting quality)
Edge Profile:	Rounded

Device Layer

Type / Dopant	P / Boron
Orientation incl. off-orientation:	{100} ± 0.5°
Resistivity:	1 – 10 Ohmcm
Thickness:	100 ± 0.7µm

Buried Oxide

Oxide Thickness:	2.00µm ± 3%

Handle Wafer

Type / Dopant	P / Boron
Orientation incl. off-orientation:	{100} ± 0.5°
Resistivity:	1 – 10 Ohmcm
Thickness:	380 ± 5µm
Back Surface:	Polished, without remaining oxide on backside
Laser Marking:	Wafers backside according to PO